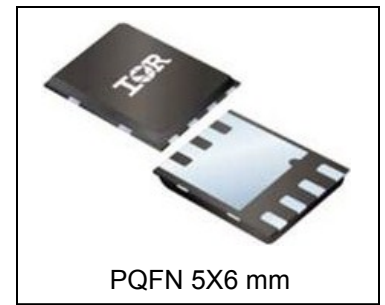
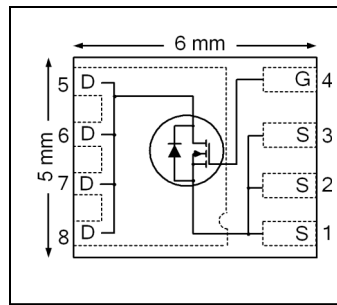


HEXFET® Power MOSFET

| | | |
|--|-------------|-----------|
| V_{DSS} | 100 | V |
| R_{DS(on)} max (@ V _{GS} = 10V) | 16.4 | mΩ |
| Q_g (typical) | 13 | nC |
| R_g (typical) | 2.1 | Ω |
| I_D (@T _{C(Bottom)} = 25°C) | 35 | A |



Applications

- Primary Switch for High Frequency 48V/60V Telecom DC-DC Power Supplies
- Secondary Side Synchronous Rectifier

Features

| |
|---|
| Low R _{DS(ON)} (< 16.4mΩ) |
| Low Thermal Resistance to PCB (<3.2°C/W) |
| 100% R _g Tested |
| Low Profile (<1.05 mm) |
| Industry-Standard Pinout |
| Compatible with Existing Surface Mount Techniques |
| RoHS Compliant, Halogen-Free |
| MSL1 |

results in
⇒

Benefits

| |
|----------------------------|
| Lower Conduction Losses |
| Increased Power Density |
| Increased Reliability |
| Increased Power Density |
| Multi-Vendor Compatibility |
| Easier Manufacturing |
| Environmentally Friendlier |
| Increased Reliability |

| Base part number | Package Type | Standard Pack | | Orderable Part Number |
|------------------|-----------------|---------------|----------|-----------------------|
| | | Form | Quantity | |
| IRFH7194PbF | PQFN 5mm x 6 mm | Tape and Reel | 4000 | IRFH7194TRPbF |

Absolute Maximum Ratings

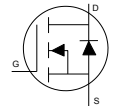
| | Parameter | Max. | Units |
|---|---|--------------|-------|
| V _{GS} | Gate-to-Source Voltage | ± 20 | V |
| I _D @ T _A = 25°C | Continuous Drain Current, V _{GS} @ 10V | 11 | A |
| I _D @ T _{C(Bottom)} = 25°C | Continuous Drain Current, V _{GS} @ 10V | 35 | |
| I _D @ T _{C(Bottom)} = 100°C | Continuous Drain Current, V _{GS} @ 10V | 22 | |
| I _{DM} | Pulsed Drain Current ① | 140 | |
| P _D @ T _A = 25°C | Power Dissipation | 3.6 | W |
| P _D @ T _{C(Bottom)} = 25°C | Power Dissipation | 39 | |
| | Linear Derating Factor | 0.03 | W/°C |
| T _J | Operating Junction and | -55 to + 150 | °C |
| T _{STG} | Storage Temperature Range | | |

Notes ① through ⑤ are on page 8

Static @ T_J = 25°C (unless otherwise specified)

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|-------------------------------------|---|------|------|------|-------|---|
| BV _{DSS} | Drain-to-Source Breakdown Voltage | 100 | — | — | V | V _{GS} = 0V, I _D = 250μA |
| ΔBV _{DSS} /ΔT _J | Breakdown Voltage Temp. Coefficient | — | 78 | — | mV/°C | Reference to 25°C, I _D = 1mA |
| R _{DS(on)} | Static Drain-to-Source On-Resistance | — | 13.7 | 16.4 | mΩ | V _{GS} = 10V, I _D = 21A ③ |
| V _{GS(th)} | Gate Threshold Voltage | 2.0 | — | 3.6 | V | V _{DS} = V _{GS} , I _D = 50μA |
| ΔV _{GS(th)} | Gate Threshold Voltage Coefficient | — | -5.2 | — | mV/°C | |
| I _{DSS} | Drain-to-Source Leakage Current | — | — | 1.0 | μA | V _{DS} = 80V, V _{GS} = 0V |
| I _{GSS} | Gate-to-Source Forward Leakage | — | — | 100 | nA | V _{GS} = 20V |
| | Gate-to-Source Reverse Leakage | — | — | -100 | nA | V _{GS} = -20V |
| g _{fs} | Forward Transconductance | 45 | — | — | S | V _{DS} = 25V, I _D = 21A |
| Q _g | Total Gate Charge | — | 13 | 19 | nC | V _{DS} = 50V V _{GS} = 10V I _D = 21A |
| Q _{gs1} | Pre-V _{th} Gate-to-Source Charge | — | 1.8 | — | | |
| Q _{gs2} | Post-V _{th} Gate-to-Source Charge | — | 0.9 | — | | |
| Q _{gd} | Gate-to-Drain Charge | — | 4.3 | — | | |
| Q _{godr} | Gate Charge Overdrive | — | 6.0 | — | | |
| Q _{sw} | Switch Charge (Q _{gs2} + Q _{gd}) | — | 5.2 | — | | |
| Q _{oss} | Output Charge | — | 40 | — | nC | V _{DS} = 50V, V _{GS} = 0V |
| R _G | Gate Resistance | — | 2.1 | — | Ω | |
| t _{d(on)} | Turn-On Delay Time | — | 2.7 | — | ns | V _{DD} = 50V, V _{GS} = 10V I _D = 21A R _G = 1.0Ω |
| t _r | Rise Time | — | 3.3 | — | | |
| t _{d(off)} | Turn-Off Delay Time | — | 8.0 | — | | |
| t _f | Fall Time | — | 2.5 | — | | |
| C _{iss} | Input Capacitance | — | 733 | — | pF | V _{GS} = 0V V _{DS} = 50V f = 1.0MHz |
| C _{oss} | Output Capacitance | — | 374 | — | | |
| C _{rss} | Reverse Transfer Capacitance | — | 11 | — | | |

Diode Characteristics

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|-----------------|--|------|------|------|-------|--|
| I _S | Continuous Source Current (Body Diode) | — | — | 35 | A | MOSFET symbol showing the integral reverse p-n junction diode.  |
| I _{SM} | Pulsed Source Current (Body Diode) ① | — | — | 140 | A | |
| V _{SD} | Diode Forward Voltage | — | 0.8 | 1.3 | V | T _J = 25°C, I _S = 21A, V _{GS} = 0V ③ |
| t _{rr} | Reverse Recovery Time | — | 30 | 45 | ns | T _J = 25°C, I _F = 21A, V _{DD} = 50V |
| Q _{rr} | Reverse Recovery Charge | — | 26 | 39 | nC | di/dt = 100A/μs ③ |

Avalanche Characteristics

| | Parameter | Typ. | Max. | Units |
|-------------------------------------|---------------------------------|------|------|-------|
| E _{AS} (Thermally limited) | Single Pulse Avalanche Energy ② | — | 220 | mJ |
| I _{AR} | Avalanche Current ① | — | 12 | A |

Thermal Resistance

| | Parameter | Typ. | Max. | Units |
|---------------------------|-----------------------|------|------|-------|
| R _{θJC} (Bottom) | Junction-to-Case ④ | — | 3.2 | °C/W |
| R _{θJC} (Top) | Junction-to-Case ④ | — | 22 | |
| R _{θJA} | Junction-to-Ambient ⑤ | — | 35 | |
| R _{θJA} (<10s) | Junction-to-Ambient ⑤ | — | 20 | |

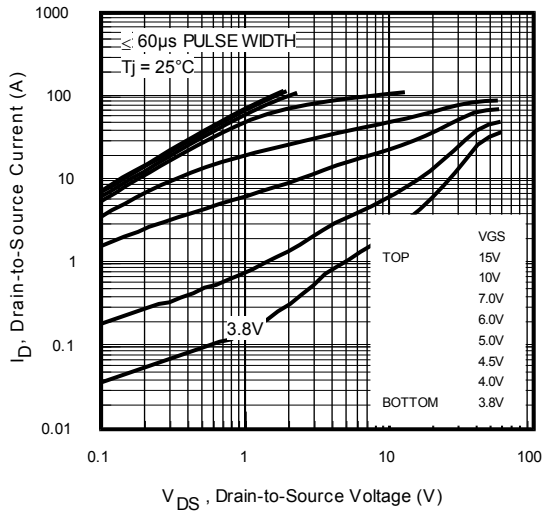


Fig 1. Typical Output Characteristics

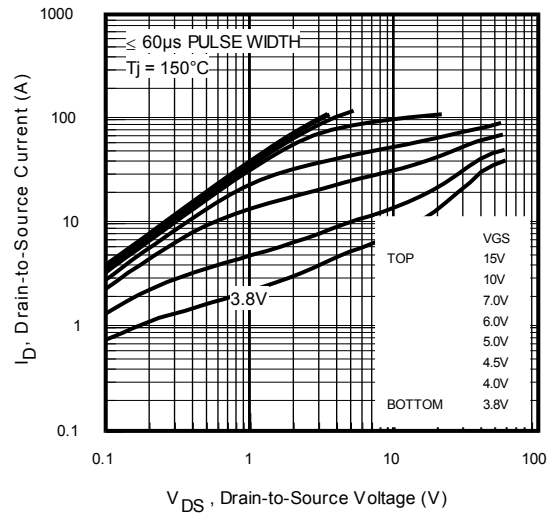


Fig 2. Typical Output Characteristics

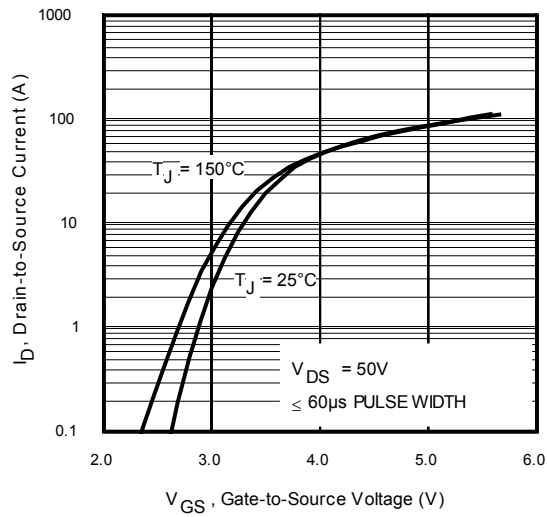


Fig 3. Typical Transfer Characteristics

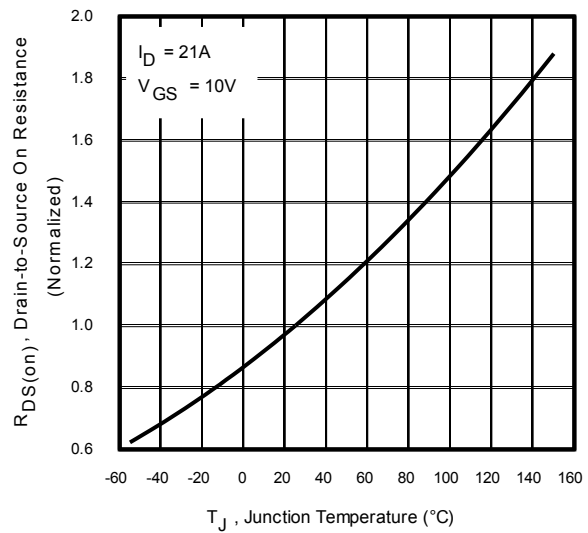


Fig 4. Normalized On-Resistance vs. Temperature

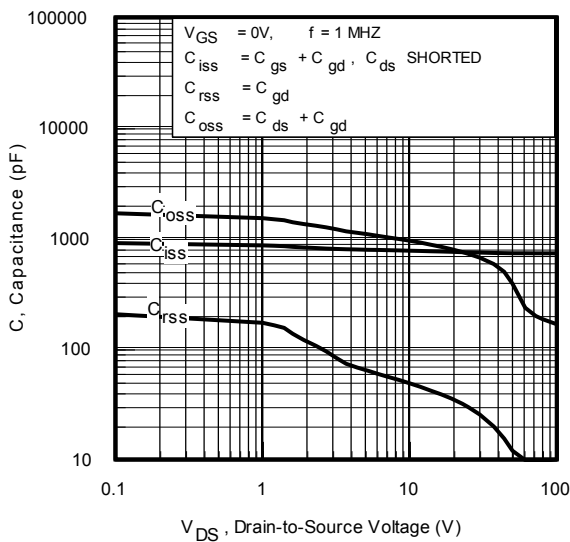


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

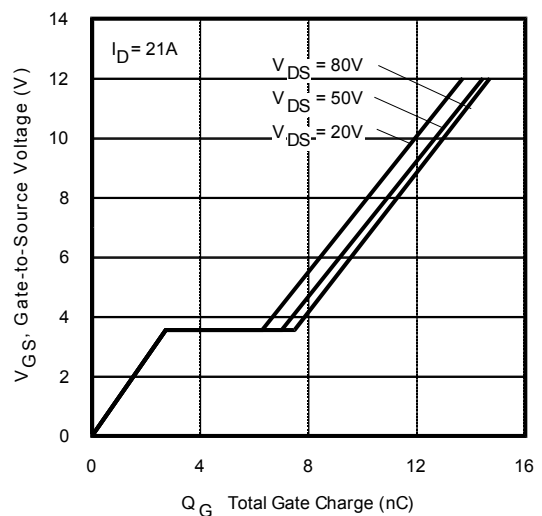


Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

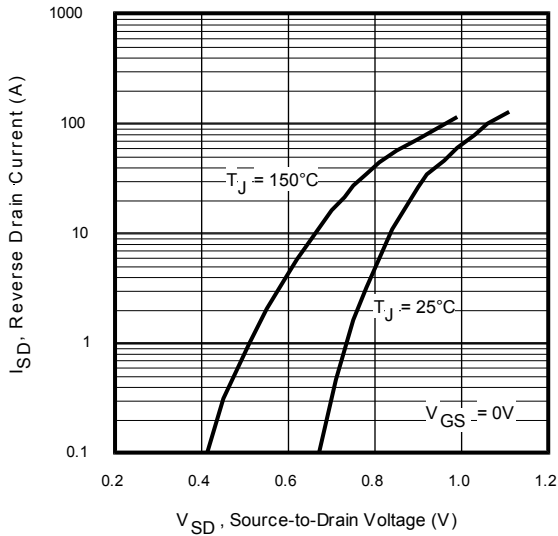


Fig 7. Typical Source-Drain Diode Forward Voltage

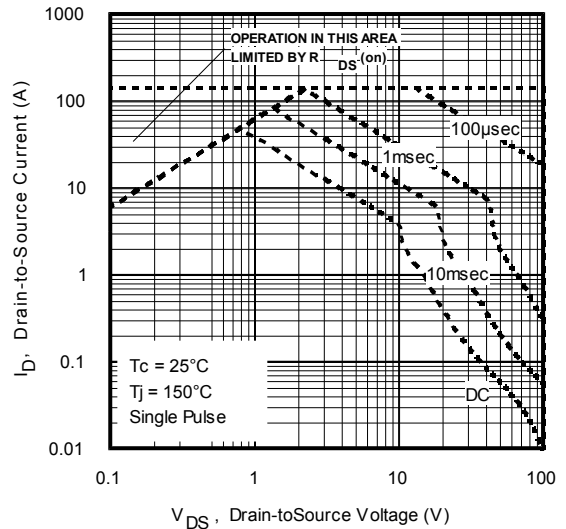


Fig 8. Maximum Safe Operating Area

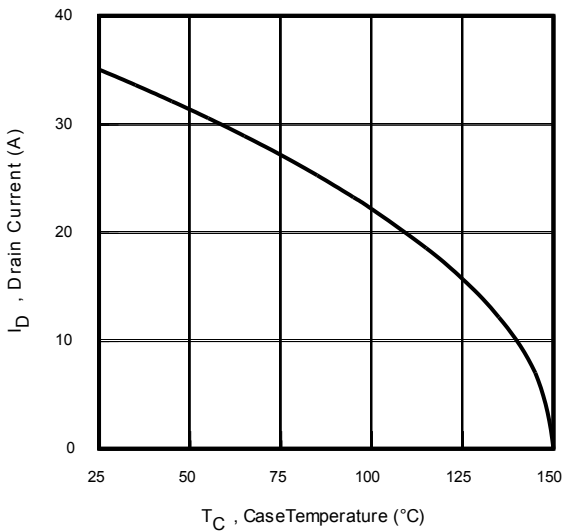


Fig 9. Maximum Drain Current vs. Case Temperature

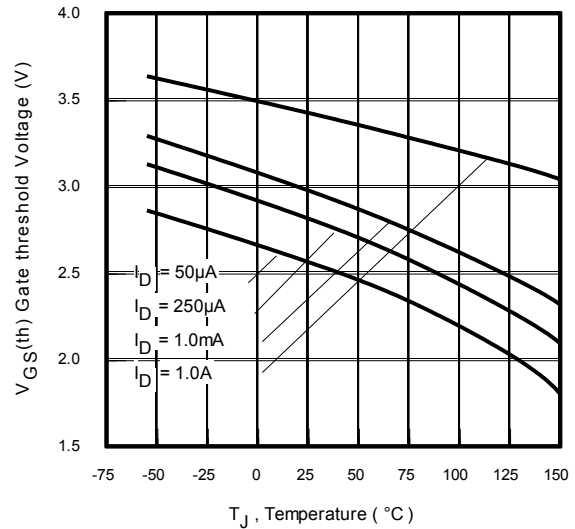


Fig 10. Threshold Voltage vs. Temperature

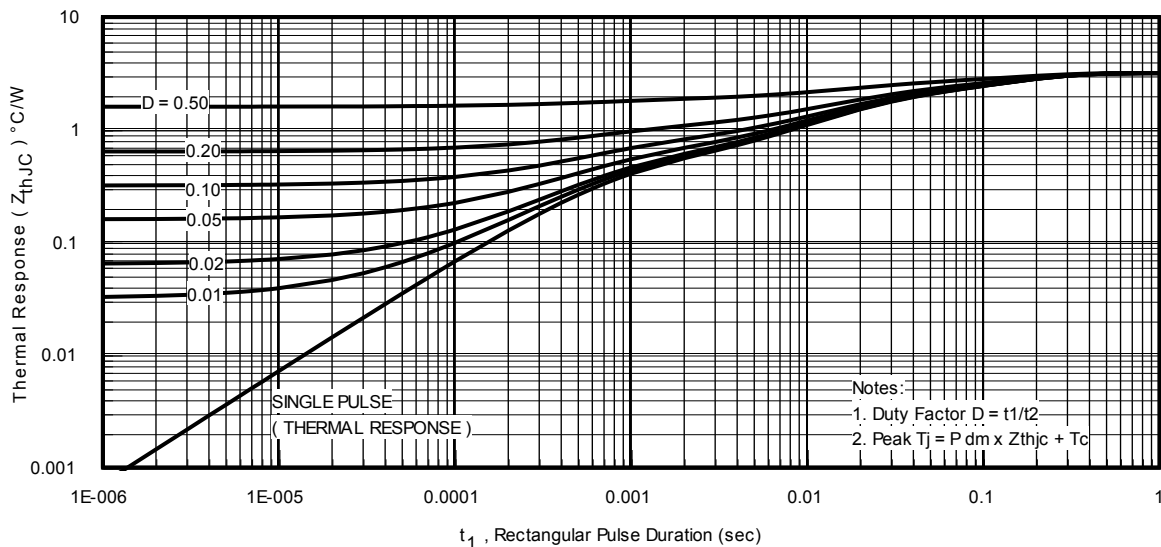


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

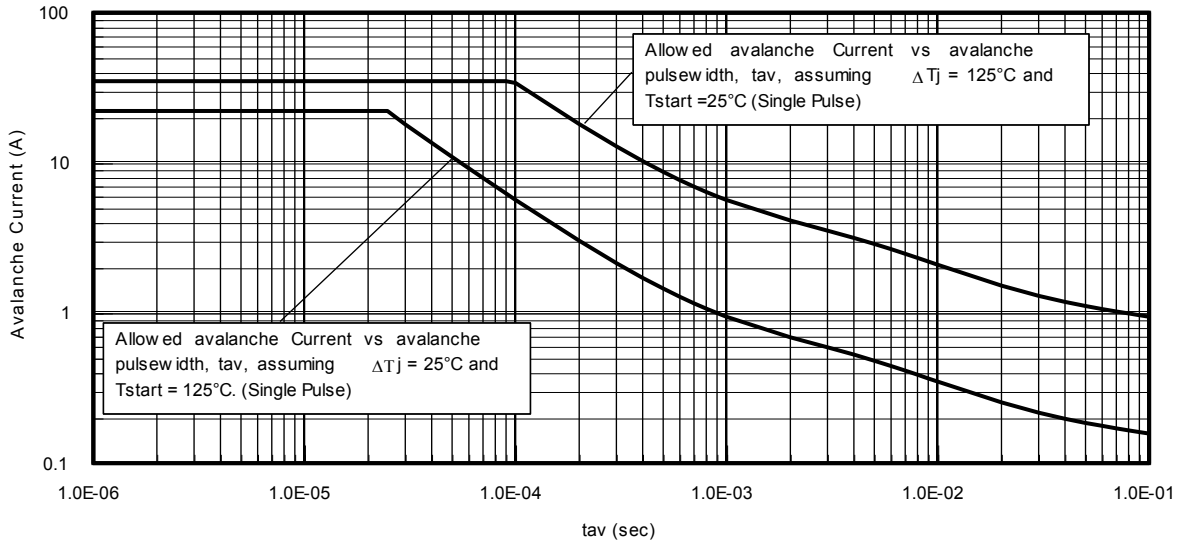


Fig 12. Typical Avalanche Current vs. Pulse Width

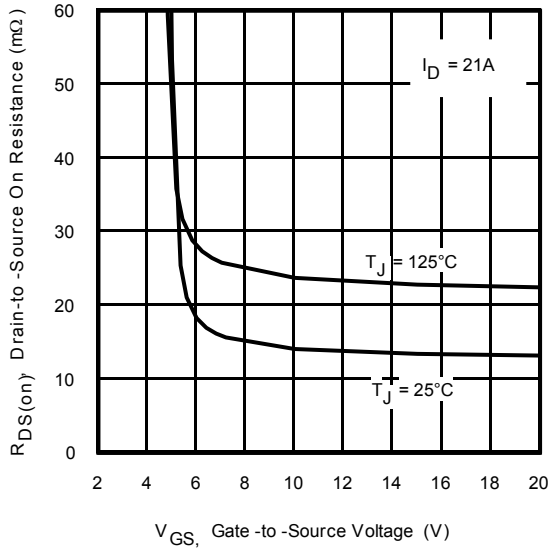


Fig 13. On-Resistance vs. Gate Voltage

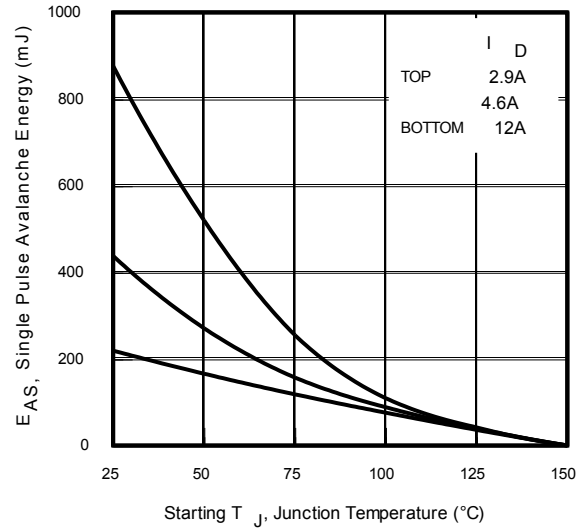
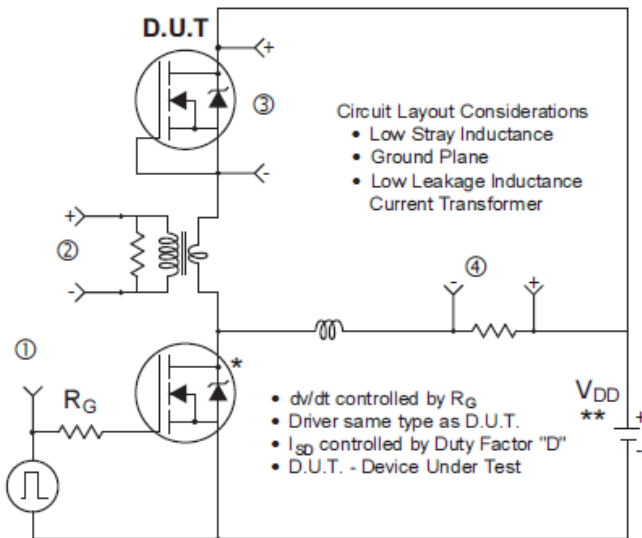
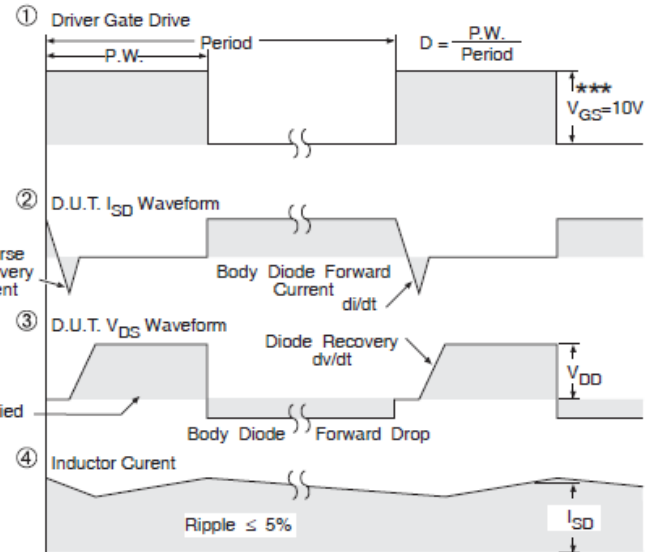


Fig 14. Maximum Avalanche Energy vs. Drain Current



* Use P-Channel Driver for P-Channel Measurements

** Reverse Polarity for P-Channel



*** $V_{GS} = 5V$ for Logic Level Devices

Fig 15. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

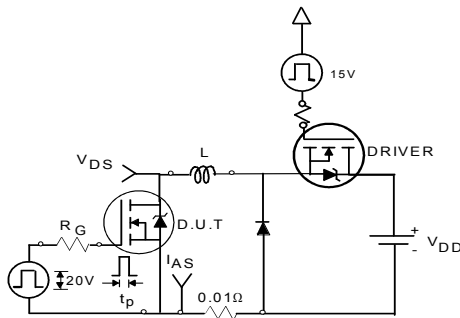


Fig 16a. Unclamped Inductive Test Circuit

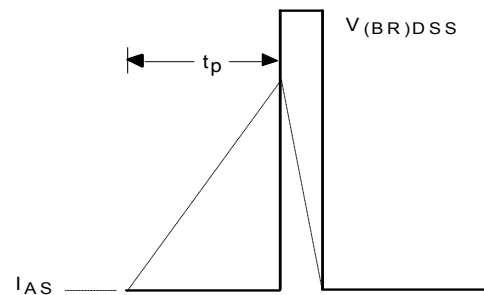


Fig 16b. Unclamped Inductive Waveforms

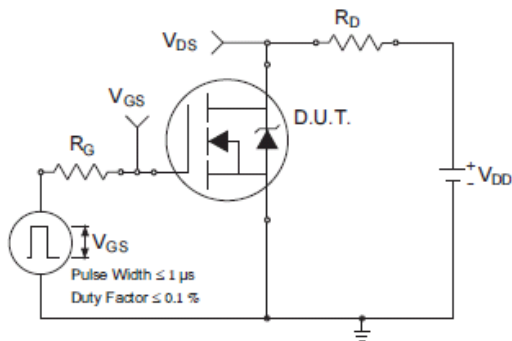


Fig 17a. Switching Time Test Circuit

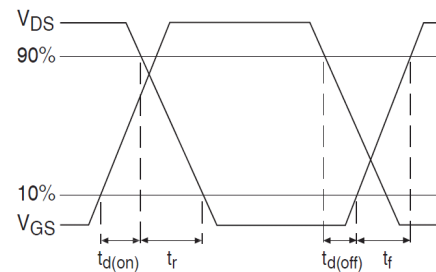


Fig 17b. Switching Time Waveforms

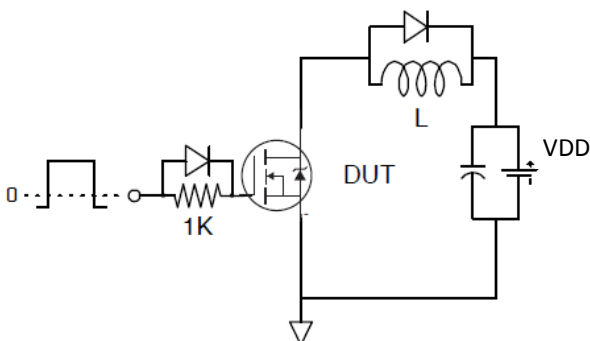


Fig 18. Gate Charge Test Circuit

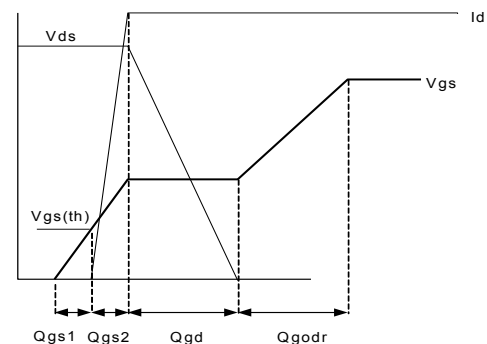
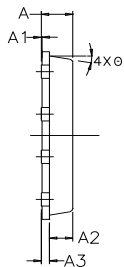
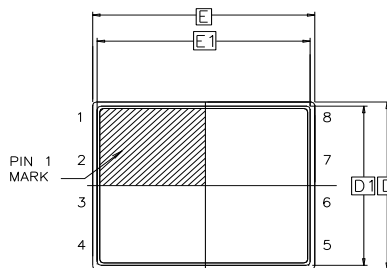


Fig 19. Gate Charge Waveform

PQFN 5x6 Outline "B" Package Details

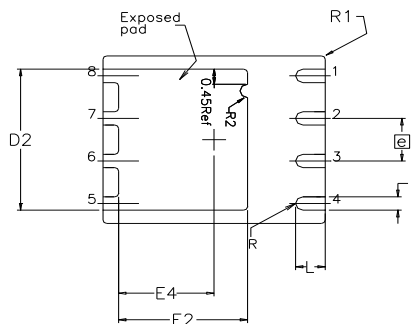


SIDE VIEW



TOP VIEW

| SYMBOL | DIM | MIN | NOM | MAX |
|--------|-----|-------|-----------|-------|
| A | | 0.800 | 0.830 | 1.05 |
| A1 | | 0.000 | 0.020 | 0.050 |
| A2 | | 0.580 | 0.630 | 0.680 |
| A3 | | | 0.254 REF | |
| Ø | | 0* | 10* | 12* |
| b | | 0.350 | 0.400 | 0.470 |
| D | | 4.850 | 5.000 | 5.150 |
| D1 | | 4.675 | 4.750 | 5.000 |
| D2 | | 3.700 | 4.210 | 4.300 |
| e | | | 1.270 BSC | |
| E | | 5.850 | 6.000 | 6.150 |
| E1 | | 5.675 | 5.750 | 6.000 |
| E2 | | 3.380 | 3.480 | 3.760 |
| E4 | | 2.480 | 2.580 | 2.680 |
| L | | 0.550 | 0.800 | 0.900 |
| R | | | 0.200 REF | |
| R1 | | | 0.100 REF | |
| R2 | | 0.150 | 0.200 | 0.250 |

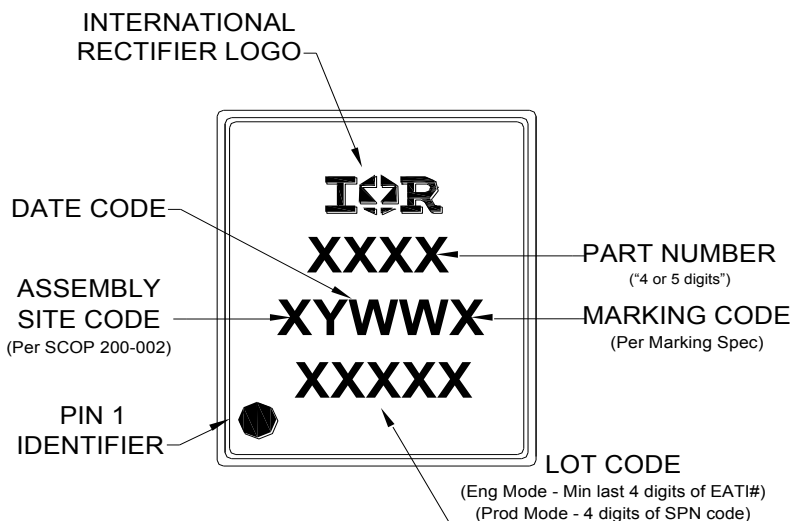


BOTTOM VIEW

For more information on board mounting, including footprint and stencil recommendation, please refer to application note AN-1136: <http://www.irf.com/technical-info/appnotes/an-1136.pdf>

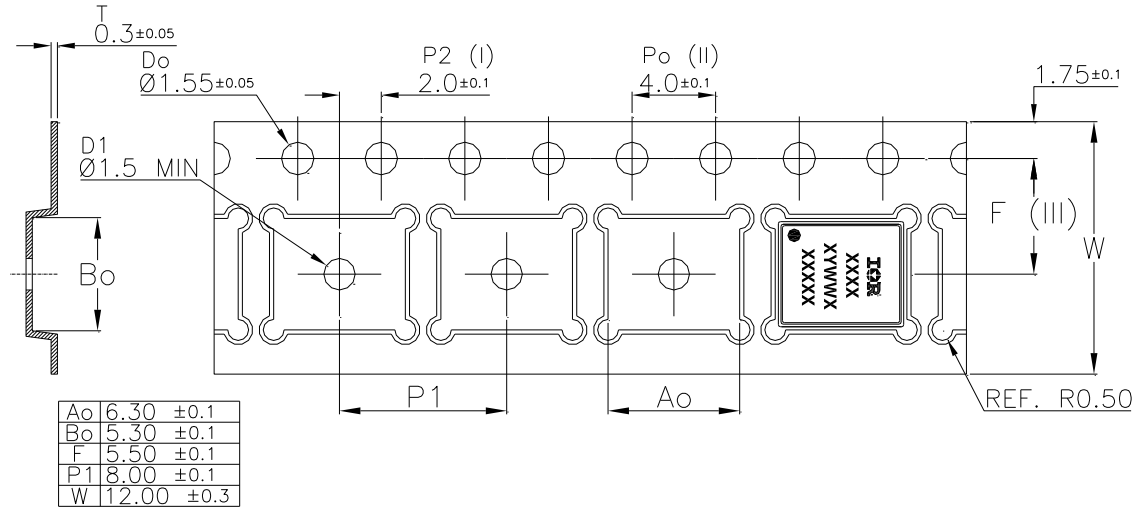
For more information on package inspection techniques, please refer to application note AN-1154: <http://www.irf.com/technical-info/appnotes/an-1154.pdf>

PQFN 5x6 Outline "B" Part Marking



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

PQFN 5x6 Outline "B" Tape and Reel



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

Qualification Information†

| | | |
|----------------------------|--|----------------------------------|
| Qualification Level | Industrial (per JEDEC JESD47F†† guidelines) | |
| Moisture Sensitivity Level | PQFN 5mm x 6mm | MSL1 (per JEDEC J-STD-020D††) |
| RoHS Compliant | Yes | |

† Qualification standards can be found at International Rectifier’s web site: <http://www.irf.com/product-info/reliability/>

†† Applicable version of JEDEC standard at the time of product release.

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^\circ\text{C}$, $L = 3.0\text{mH}$, $R_G = 50\Omega$, $I_{AS} = 12\text{A}$.
- ③ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.
- ④ R_θ is measured at T_J of approximately 90°C .
- ⑤ When mounted on 1 inch square PCB (FR-4). Please refer to AN-994 for more details:
<http://www.irf.com/technical-info/appnotes/an-994.pdf>

单击下面可查看定价，库存，交付和生命周期等信息

[>>Infineon Technologies\(英飞凌\)](#)